

Silicon NPN Power Transistors

2SC1161

DESCRIPTION

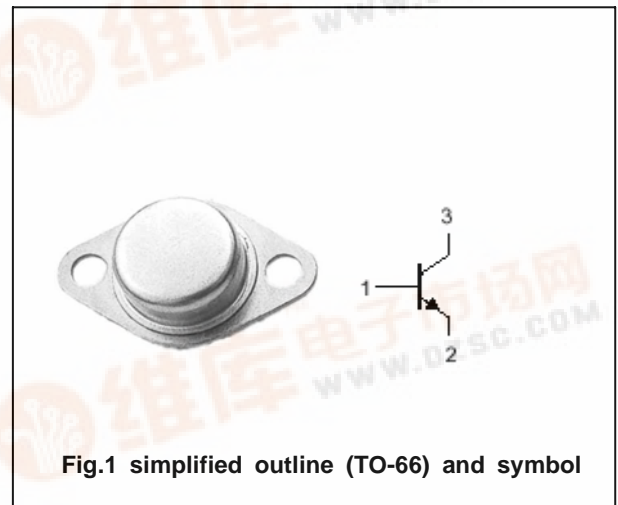
- With TO-66 package
- Low collector saturation voltage

APPLICATIONS

- For low frequency high voltage power amplifier TV vertical deflection output applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	200	V
V _{CEO}	Collector-emitter voltage	Open base	120	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _c	Collector current		1	A
P _D	Total power dissipation	T _C =25°C	15	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	120			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA ; I _B =50mA			1.5	V
V _{BE sat}	Base-emitter saturation voltage	I _C =500mA ; I _B =50mA			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =120V ; I _E =0			1.0	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =6V ; I _C =0			1.0	μ A
h _{FE}	DC current gain	I _C =200mA ; V _{CE} =5V	30		200	
f _T	Transition frequency	I _C =200mA ; V _{CE} =10V	5			MHz

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PACKAGE OUTLINE

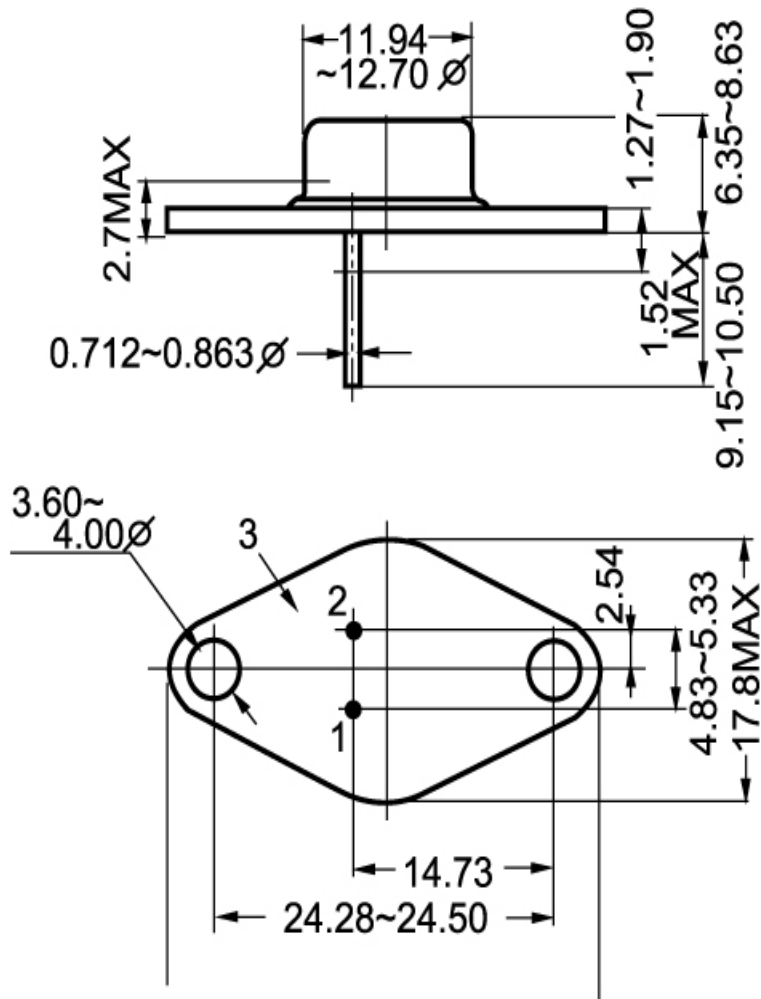


Fig.2 outline dimensions